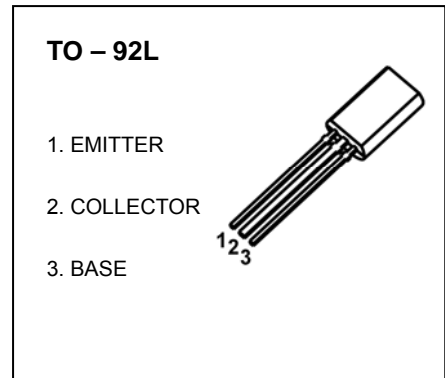


## TO-92L Plastic-Encapsulate Transistors

### 2SB562 TRANSISTOR (PNP)

#### FEATURES

- Low Frequency Power Amplifier
- Complementary Pair with 2SD468



#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-25	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-20	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-1	A
P <sub>C</sub>	Collector Power Dissipation	750	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	167	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10μA, I <sub>E</sub> =0	-25			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-20			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-20V, I <sub>E</sub> =0			-1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-1	μA
DC current gain	h <sub>FE</sub> *	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A	85		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =-0.8A, I <sub>B</sub> =-0.08A			-0.5	V
Base-emitter voltage	V <sub>BE</sub> *	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A			-1	V
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		38		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A		350		MHz

\*Pulse test

#### CLASSIFICATION OF h<sub>FE</sub>

RANK	B	C
RANGE	85-170	120-240